

## Loadless 4T SRAM cell with PMOS drivers

### ABSTRACT

5 The instant invention comprises a memory cell with PMOS drive  
transistors (170, 180) and NMOS pass transistors (150, 160). A  
NMOS transistor is connected between a storage node (230) and a  
bitline (200). The NMOS transistor is gated by the wordline  
(190). A PMOS drive transistor (180) is connected between the  
10 storage node (230) and a supply voltage (255).

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